

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of

Seiichi MIYAZAKI

Application No.: U.S. National Stage of PCT/JP00/09185

Filed: August 15, 2001

Docket No.: 110386

For: ETCHANT, ETCHING METHOD AND SEMICONDUCTOR SILICON WAFER

PRELIMINARY AMENDMENT

Director of the U.S. Patent and Trademark Office  
Washington, D. C. 20231

Sir:

Prior to initial examination, please amend the above-identified application as follows:

IN THE CLAIMS:

Please cancel claims 1-20 without prejudice to or disclaimer of the subject matter contained therein.

Please add new claims 21-42 as follows:

- A1
- 21. An etchant of a semiconductor material, being prepared by immersing stainless steel in an alkali aqueous solution for not less than 10 hours. --
  - 22. The etchant as claimed in claim 21, wherein the alkali is sodium hydroxide. --
  - 23. The etchant as claimed in claim 21, wherein the stainless steel is one of (SUS304) and (SUS316). --
  - 24. The etchant as claimed in claim 21, wherein a temperature of the alkali aqueous solution is between 70°C and 90°C. --